



N-Channel 20-V (D-S) MOSFET

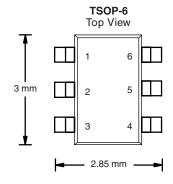
PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)		
	0.027 at V _{GS} = 4.5 V	6.8		
20	0.032 at V _{GS} = 2.5 V	6.3		
	0.038 at V _{GS} = 1.8 V	5.7		

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS directive 2002/95/EC

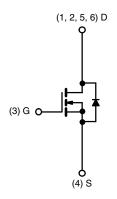






Ordering Information: Si3460DV-T1-E3 (Lead (Pb)-free)

Si3460DV-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	T _A = 25 °C, unle	ss otherwise r	noted		
Parameter		Symbol	5 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	20		V
Gate-Source Voltage		V_{GS}	± 8		
Continuous Dusin Compant /T 450 00\8	T _A = 25 °C	I _D	6.8	5.1	
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		5.4	4.1	
Pulsed Drain Current		I _{DM}	20		Α
Continuous Source Current (Diode Conduction) ^a		I _S	1.7	0.9	
Maniana Banas Birata atian	T _A = 25 °C	P _D	2.0	1.1	W
Maximum Power Dissipation ^a	T _A = 70 °C		1.3	0.73	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Manipulation to Australia	t ≤ 5 s	R _{thJA}	45	62.5	°C/W	
Maximum Junction-to-Ambient ^a	Steady State	' ¹thJA	90	110		
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	25	30		

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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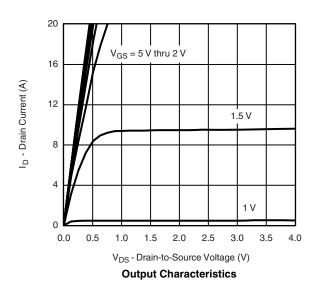
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static	•						
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 1 \text{ mA}$	0.45			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA	
Zava Cata Valtaga Dvain Curvent	I _{DSS}	V _{DS} = 16 V, V _{GS} = 0 V			1		
Zero Gate Voltage Drain Current		V _{DS} = 16 V, V _{GS} = 0 V, T _J = 70 °C			5	μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	20			Α	
		$V_{GS} = 4.5 \text{ V}, I_D = 5.1 \text{ A}$		0.023	0.027		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 2.5 V, I _D = 4.7 A 0.027 0.032				Ω	
		$V_{GS} = 1.8 \text{ V}, I_D = 2 \text{ A}$		0.032	0.038		
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 10 \text{ V}, I_D = 5.1 \text{ A}$		25		S	
Diode Forward Voltage ^a	V_{SD}	I _S = 1.7 A, V _{GS} = 0 V		0.8	1.2	V	
Dynamic ^b							
Total Gate Charge	Q_g			13.5	20		
Gate-Source Charge	Q_{gs}	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 5.1 \text{ A}$		2.3		nC	
Gate-Drain Charge	Q_{gd}			2.2			
Gate Resistance	R_g		0.5		2.9	Ω	
Turn-On Delay Time	t _{d(on)}			15	30		
Rise Time	t _r	V_{DD} = 10 V, R_L = 10 Ω		30	60	ns	
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ 1 A, V_{GEN} = 4.5 V, R_g = 6 Ω		70	140		
Fall Time	t _f			30	60		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 1.7 A, dI/dt = 100 A/μs		40	80		

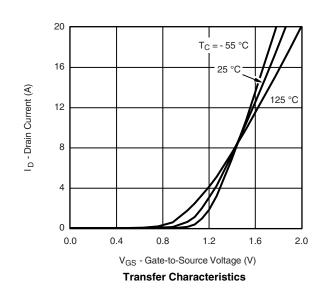
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted







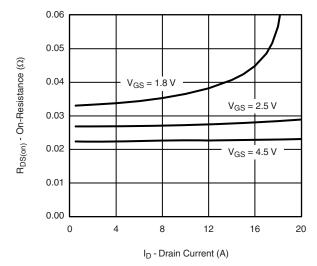




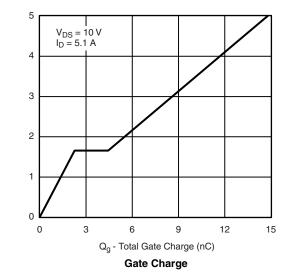
V_{GS} - Gate-to-Source Voltage (V)

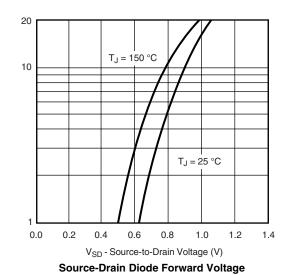
Is - Source Current (A)

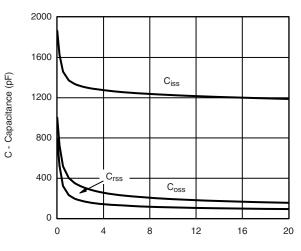
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



On-Resistance vs. Drain Current

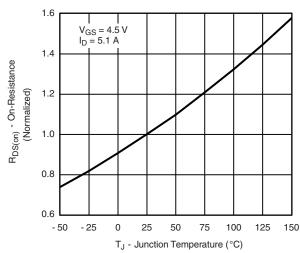




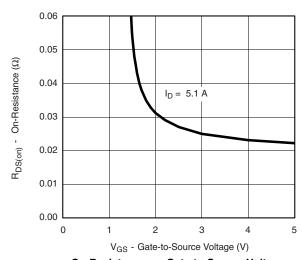


 $V_{\mbox{\footnotesize DS}}$ - Drain-to-Source Voltage (V)

Capacitance



On-Resistance vs. Junction Temperature

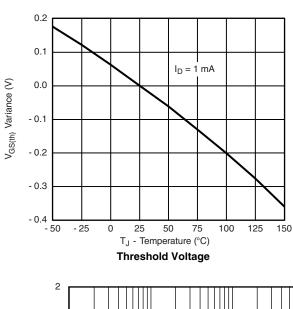


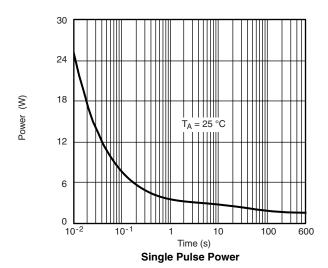
On-Resistance vs. Gate-to-Source Voltage

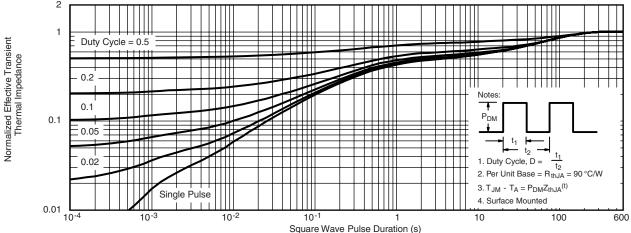
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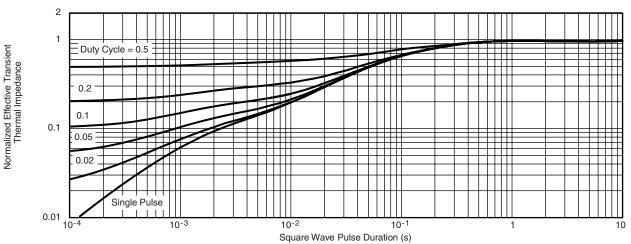
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted











Normalized Thermal Transient Impedance, Junction-to-Foot

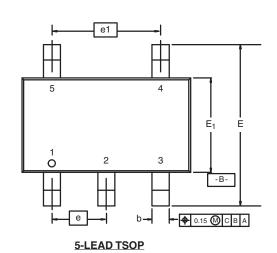
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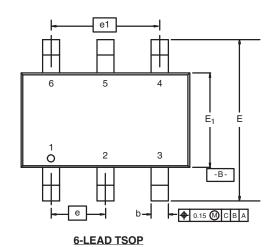


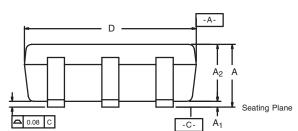


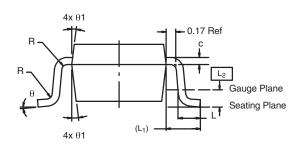
TSOP: 5/6-LEAD

JEDEC Part Number: MO-193C









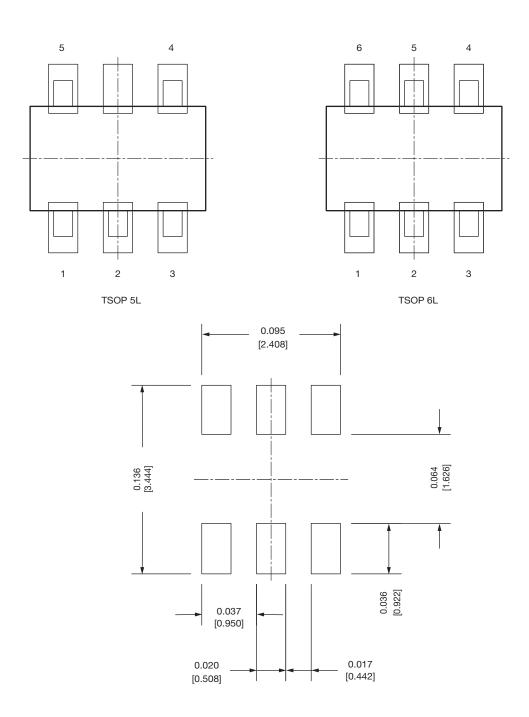
	MILLIMETERS			INCHES			
Dim	Min	Nom	Max	Min	Nom	Max	
Α	0.91	-	1.10	0.036	-	0.043	
A ₁	0.01	-	0.10	0.0004	-	0.004	
A ₂	0.90	-	1.00	0.035	0.038	0.039	
b	0.30	0.32	0.45	0.012	0.013	0.018	
С	0.10	0.15	0.20	0.004	0.006	0.008	
D	2.95	3.05	3.10	0.116	0.120	0.122	
Е	2.70	2.85	2.98	0.106	0.112	0.117	
E ₁	1.55	1.65	1.70	0.061	0.065	0.067	
е	0.95 BSC			0.0374 BSC			
e ₁	1.80	1.90	2.00	0.071 0.075 0.0			
L	0.32	-	0.50	0.012	-	0.020	
L ₁		0.60 Ref		0.024 Ref			
L ₂	0.25 BSC			0.010 BSC			
R	0.10	-	-	0.004	-	-	
θ	0°	4°	8°	0°	4°	8°	
θ_1		7° Nom		7° Nom			
ECN: C-06593-Rev. I, 18-Dec-06 DWG: 5540							

Document Number: 71200 18-Dec-06

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Recommended Land Pattern For TSOP-5L / TSOP-6L



Note

• All dimensions are in inches (millimeter)

ECN: C22-0860-Rev. B, 24-Oct-2022 DWG: 3010



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